

Description

The ASD15CW is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers and PDA's, using monolithic silicon technology to provide fast response time and ultra low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The ASD15CW complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. The ASD15CW is assembled into a lead-free SOD-323 package and will protect one bidirectional line. These devices will fit on the same PCB pad area as an 0805 MLV device.

Features

- 250W peak pulse power (8/20µs)
- Protects one data or power line
- Ultra low leakage: nA level
- Operating voltage: 15V
- Ultra low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 Air discharge: ±30kV
 Contact discharge: ±30kV
 - IEC61000-4-5 (Lightning) 10A (8/20µs)
- RoHS Compliant

Mechanical Characteristics

- Package: SOD-323Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

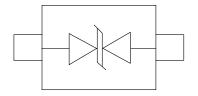
- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Peripherals
- Pagers Peripherals
- Desktop and Servers

Marking Information



Ordering Information

Dimensions and Pin Configuration



SOD-323

Part Number	Packaging	Reel Size
ASD15CW	3000/Tape & Reel	7 inch



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

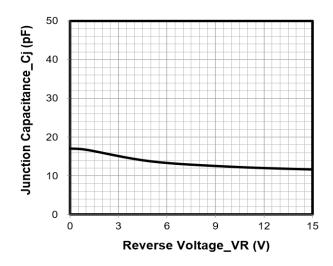
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	250	W
Peak Pulse Current (8/20μs)	IPP	10	А
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	VESD	±30 ±30	kV
Operating Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

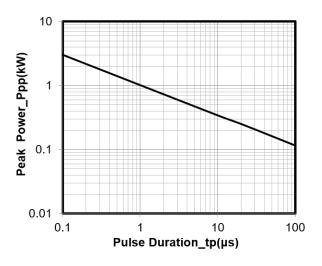
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			15	V	
Breakdown Voltage	VBR	16.5			V	IT = 1mA
Reverse Leakage Current	I _R			0.5	μΑ	VRWM = 15V
Clamping Voltage	Vc			20	V	IPP = 1A (8 x 20μs pulse)
Clamping Voltage	Vc			25	V	IPP = 10A (8 x 20µs pulse)
Junction Capacitance	CJ		17		pF	VR = 0V, f = 1MHz

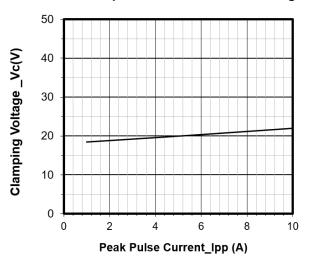


Typical Performance Characteristics (T_A=25°C unless otherwise Specified)

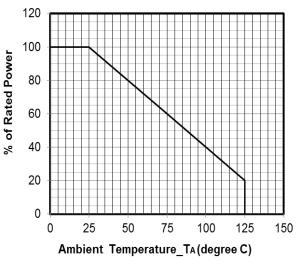




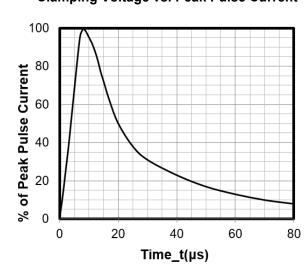
Junction Capacitance vs. Reverse Voltage



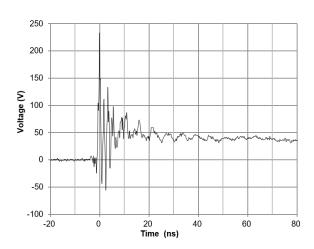
Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current



Power Derating Curve

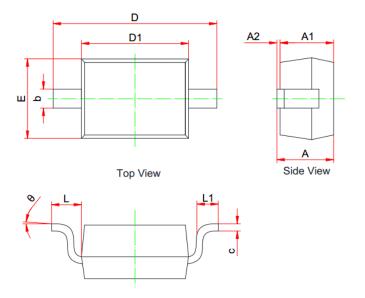


8 X 20µs Pulse Waveform

ESD Clamping Voltage 8 kV Contact per IEC61000-4-2

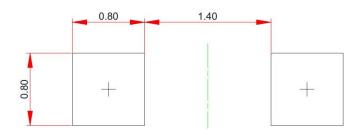


SOD-323 Package Outline Drawing



	MILLIMETERS				
	MIN	NOM	MAX		
Α	0.800		1.100		
A1	0.800		0.900		
A2	0.000		0.100		
b	0.250		0.400		
С	0.080		0.177		
D1	1.600	1.700	1.800		
D	2.300		2.800		
E	1.150		1.400		
L	0.475REF				
L1	0.100		0.500		
Θ	0°		8°		

Suggested Land Pattern



Unit: mm

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